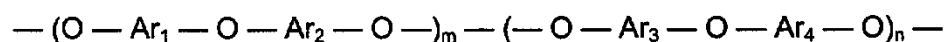


THIN FILM TRANSISTORS WITH POLY(ARYLENE ETHER) POLYMERS AS
GATE DIELECTRICS AND PASSIVATION LAYERS

ABSTRACT OF THE DISCLOSURE

The use of a poly(arylene ether) polymer as a passivation or gate dielectric layer in thin
5 film transistors. This poly(arylene ether) polymer includes polymer repeat units of the
following structure:



where Ar₁, Ar₂, Ar₃, and Ar₄ are identical or different aryl radicals, m is 0 to 1, n is 1-m,
and at least one of the aryl radicals is grafted to the backbone of the polymer

10 **Figure 1**

15

06935ZP_USA.DOC